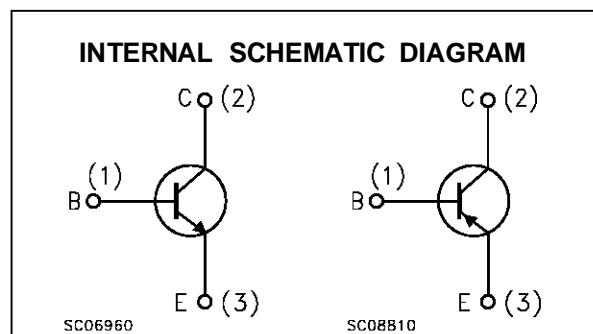
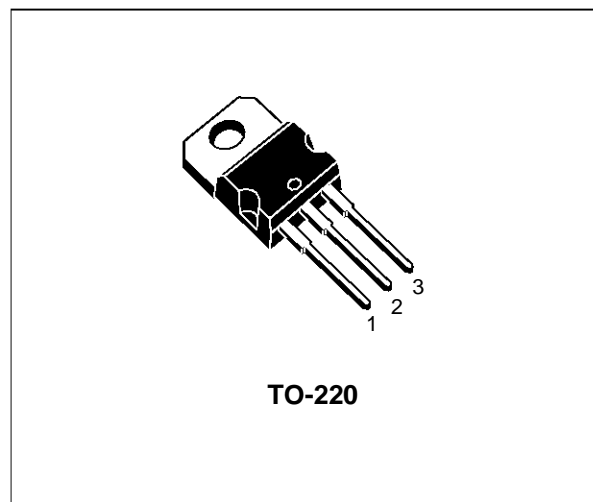


COMPLEMENTARY SILICON POWER TRANSISTORS

- TIP31A, TIP31C, TIP32A, TIP32B, AND TIP32C ARE SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The TIP31A, TIP31B and TIP31C are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intended for use in medium power linear and switching applications. The complementary PNP types are TIP32A, TIP32B and TIP32C.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit	
		NPN	TIP31A	TIP31B		TIP31C
		PNP	TIP32A	TIP32B	TIP32C	
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	80	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		5			V
I _C	Collector Current		3			A
I _{CM}	Collector Peak Current		5			A
I _B	Base Current		1			A
P _{tot}	Total Dissipation at T _{case} ≤ 25 °C T _{amb} ≤ 25 °C		40			W
			2			W
T _{stg}	Storage Temperature		-65 to 150			°C
T _j	Max. Operating Junction Temperature		150			°C

For PNP types voltage and current values are negative.

TIP31A/TIP31B/TIP31C/TIP32A/TIP32B/TIP32C

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

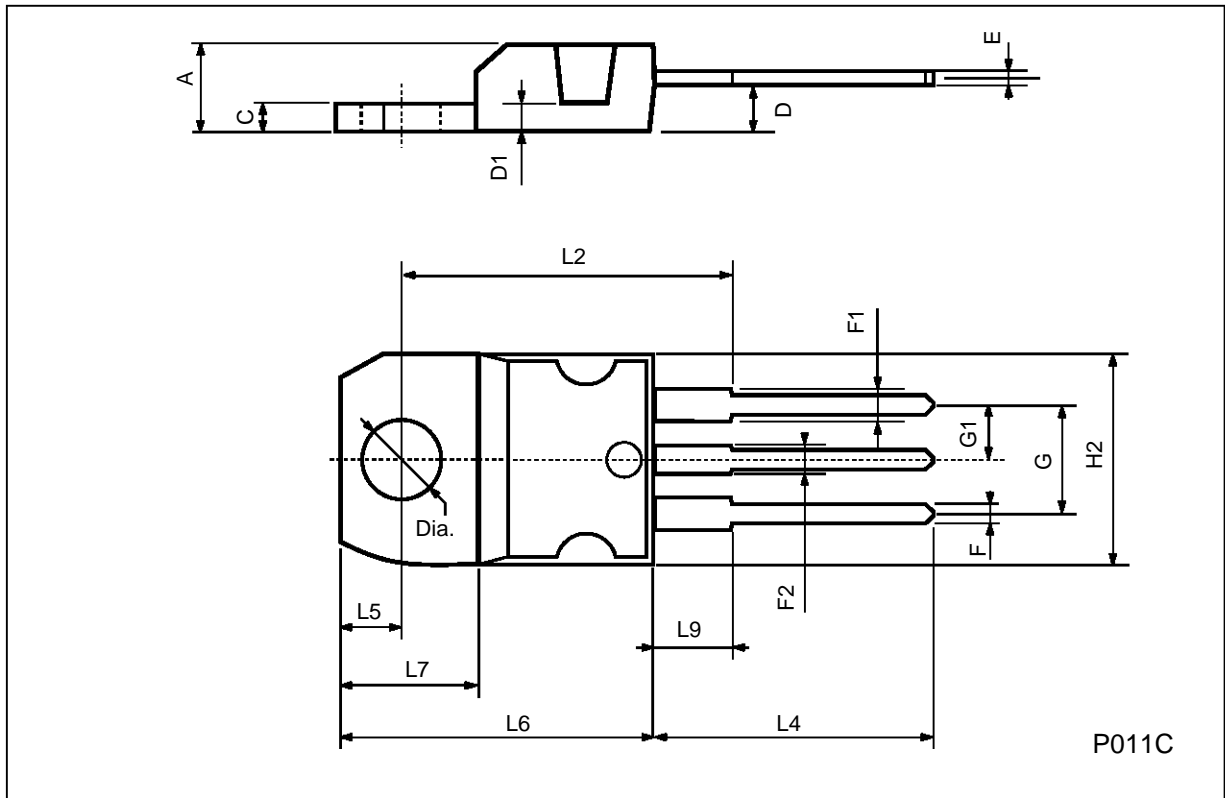
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _B = 0)	for TIP31A/32A V _{CE} = 30 V for TIP31B/31C/32B/32C V _{CB} = 60 V			0.3	mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for TIP31A/32A V _{CE} = 60 V for TIP31B/32B V _{CE} = 80 V for TIP31C/32C V _{CE} = 100 V			0.2	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP31A/32A for TIP31B/32B for TIP31C/32C	60 80 100			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 3 A I _B = 375 mA			1.2	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 3 A V _{CE} = 4 V			1.8	V
h _{FE} *	DC Current Gain	I _C = 1 A V _{CE} = 4 V I _C = 3 A V _{CE} = 4 V	25 10		50	
h _{fe}	Small Signal Current Gain	I _C = 0.5 A V _{CE} = 10 V f = 1 KHz I _C = 0.5 A V _{CE} = 10 V f = 1 MHz	20 3			

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %
For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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